NSN 5961-01-130-1885

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View Online at https://aerobasegroup.com/nsn/5961-01-130-1885

Inclosure Material:

Metal

Overall Length:

0.328 inches

Overall Diameter:

0.875 inches

End Application:

Satellite com

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact-darlington connected

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-3

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

-80.0 collector to base voltage/static/emitter open and -7.0 emitter to base voltage, static, collector open and -80.0 collector to emitter voltage/static/base open

Current Rating Per Characteristic:

-20.00 amperes source cutoff current and -0.50 amperes source cutoff current

Power Rating Per Characteristic:

175.0 watts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

175.0 degrees celsius ambient air

Special Features:

Junction pattern arrangement: pnp

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

1 case and 2 pin

Specification Data:

81349-mil-s-19500/505 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0

